GaNPOWER

GaNPower International Inc.

GPI65030DFN

N-channel 650V 30A GaN Power HEMT in 8X8 DFN package

Datasheet version: 2.1

Features

| BV$_{dss}$	R$_{dson}$	I$_{ds}$	Q$_g$
650 V	55 mΩ	30 A	5.8 nC

- Ultra-low R$_{DS}$(on)
- High dv/dt capability
- Extremely low input capacitance
- Zero Qrr
- Outstanding switching performance
- Low Profile

Applications

- Switching Power Applications
- Adapters, Quick Chargers

Thermal Pad

D D D D

G S1 S S

Drain (D)

Gate (G)

Kelvin Source (S1)

Source (S)

Description

These devices are N-channel 650 V Power GaN HEMTs based on proprietary E-mode GaN on silicon technology. The resulting product has extremely low on state resistance, very low input capacitance and zero reverse recovery charge making it especially suitable for applications which require superior power density, ultra-high switching frequency and outstanding efficiency.
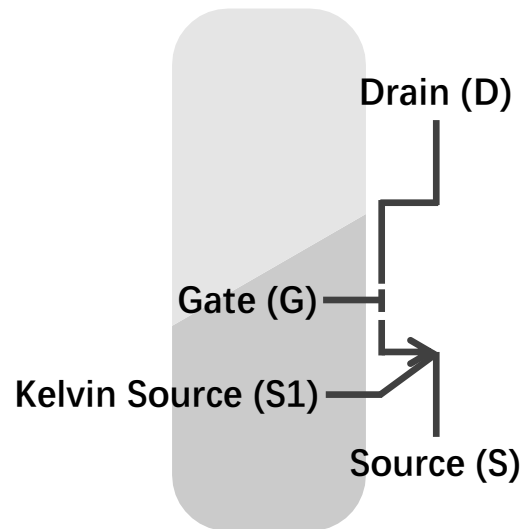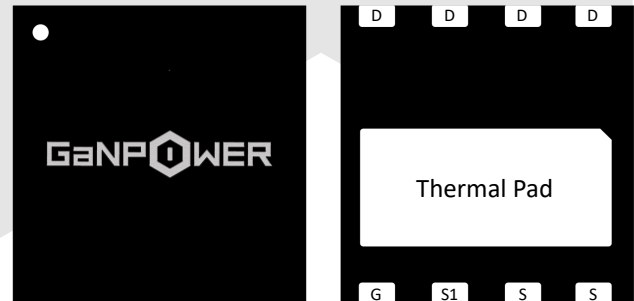
Device Characteristics

Static Parameters			Conditions	Min	Typical	Max	Unit
1	$V_{gs(TH)}$	Gate threshold voltage	$V_{ds}=V_{gs}$ Id=3.5mA	1.0	1.2	1.4	V
2	BV_{dss}	Drain-Source breakdown voltage	V_{gs}=0V I_d=25uA		650		V
3	I_{dss}	Zero gate voltage drain current, T_C = 25$\mathrm{C}°$	V_{gs}=0V V_{ds}=650V		1.5	40	uA
4	I_{gss}	Gate-Source Leakage	V_{gs} = 6V V_{ds} =0V		100	150	uA
5	R_{dson}	Static drain-source on resistance, T_C = 25$\mathrm{C}°$	V_{gs}=6V I_d=2.5A		55	65	mΩ
6	V_{sd}	Reverse conduction voltage	I_{sd}=1A V_{gs}=0V	1.65	1.85	2.0	V
7	R_g	Gate resistance	F=25MHz		1.2		Ω

Dynamic Parameters			Conditions	Min	Typical	Max	Unit
1	C_{iss}	Input capacitance	V_{gs}=0V		241		pf
	C_{oss}	Output capacitance	V_{ds}=400V		61		pf
	C_{rss}	Reverse transfer capacitance	f=1MHz		8.4		pf
3	Q_g	Gate charge	V_{ds}=400V		5.8		nC
	Q_{gs}	Gate to source charge	I_d=7.5A		1.2		nC
	Q_{gd}	Gate to drain charge	V_{gs}=6V		1.5		nC
2	Q_{rr}	Reverse recovery charge			0		nC

Switching Performance			Conditions	Min	Typical	Max	Unit
1	$t_{d(on)}$	Turn-on delay time	V_{ds}=400V		6		ns
2	t_r	Rise time	I_d=2.5A		12		ns
3	$t_{d(off)}$	Turn-off delay time	R_g=10Ω		15		ns
4	t_f	Fall time	V_{gs}=6V		13		ns

Absolute Max. Ratings

	Symbols	Parameters	Value	Unit
1	$V_{DS\text{-}max}$	Breakdown voltage transient @ T_{case}=25°C	800	V
2	$V_{GS\text{-}max}$	Gate to source max. transient voltage @ T_{case}=25°C	-12 to +7.5	V
3	$I_{ds\text{-}max}$	Drain to source DC current @ T_{case}=25°C	30	A
4	$I_{ds\text{-}max}$	Drain to source DC current @ T_{case}=100°C	24	A
5	$dv/dt_{\text{-}max}$	Drain to source voltage slew rate	200	V/nS
6	$T_{J\text{-}max}$	Max junction temperature	150	^{o}C
7	$T_{S\text{-}storage}$	Storage temperature	-55 to 150	^{o}C

Thermal and Soldering Characteristics (Typical)

	Symbols	Parameters	Value	Unit
1	R_{thJC}	Thermal resistance (junction to case)	0.95	^{o}C /W
2	T_{solder}	Reflow soldering temperature	250	^{o}C

Ordering

Order Code	Package Type	Packaging Method	Qty
GPI65030DFO	DFN surface mount, bottom cooled, 6X8 mm	Tape and Reel	3500

For more information, visit us at: www.iganpower.com, or contact us at sales@iganpower.com

GaNPower International Inc.

Electrical Performance
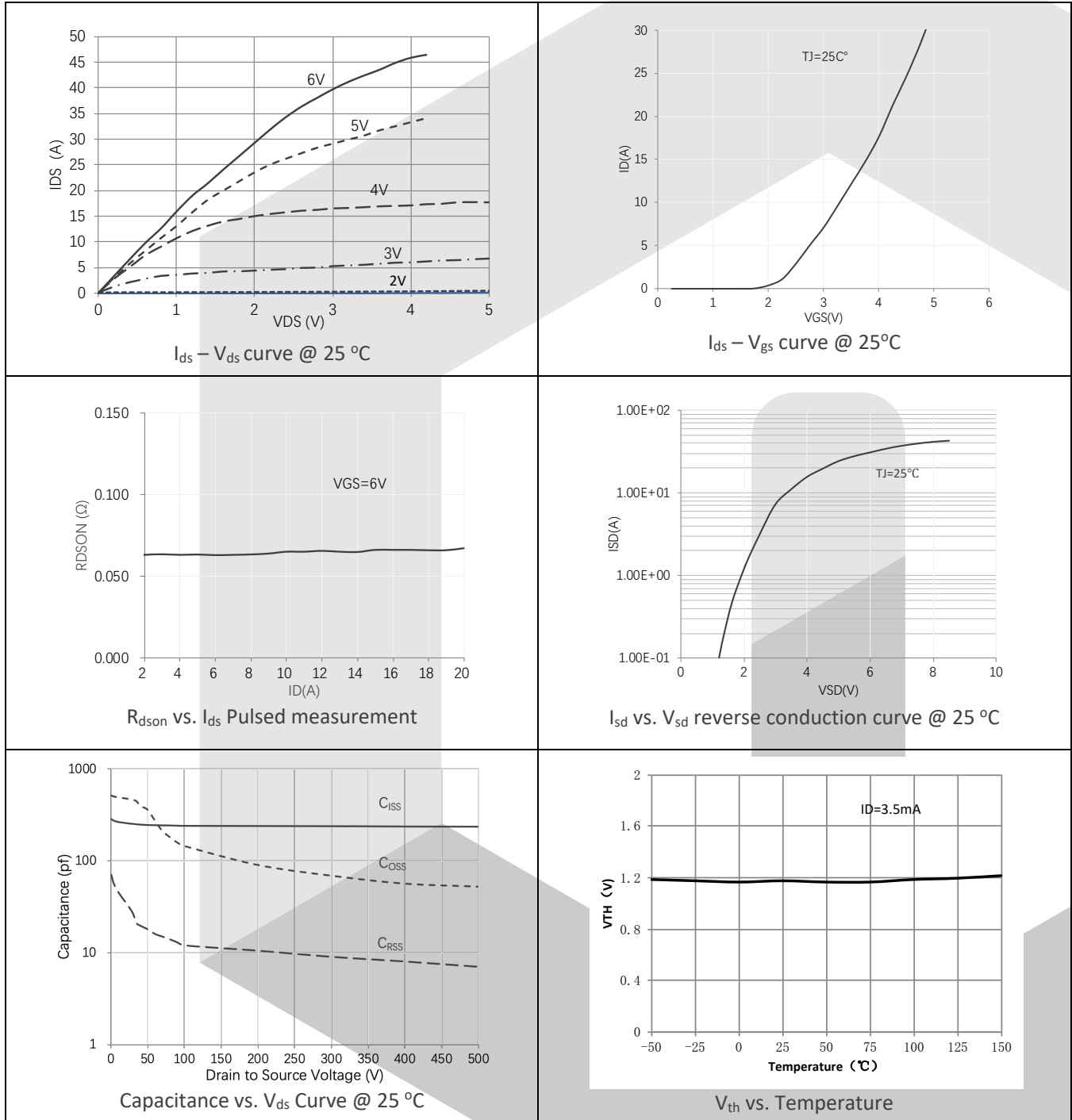
$I_{ds} - V_{ds}$ curve @ 25 °C

$I_{ds} - V_{gs}$ curve @ 25°C

R_{dson} vs. I_{ds} Pulsed measurement

I_{sd} vs. V_{sd} reverse conduction curve @ 25 °C

Capacitance vs. V_{ds} Curve @ 25 °C

V_{th} vs. Temperature

GaNPower International Inc.

IGSS vs. Temperature

I_{gss} vs. Temperature curve

Rdson Vs. Temperature

R_{dson} vs. Temperature

From Top to Bottom
25,50,75,100,125,150℃

$I_{ds} - V_{ds}$ curve @ different temperatures

TJ=150℃   6V 5V 4V 3V 2V

$I_{ds} - V_{ds}$ curve @ 150 ℃

TJ=25C°   TJ=150C°

$I_{ds} - V_{gs}$ curve @ 25℃ and 150 ℃

V_{gs} vs. Q_g curve

Package Information

Pin 8

Top view

E

D

D=8; E=8; e=1.95; b=0.97;
L=0.57; D2=6.82; E2=3.19

8LEAD DFN (8x8x0.75mm,
Pitch 1.95mm)
**IMPORTANT:Please connect
the bottom thermal pad to
the source electrode on PCB**

5   8

Bottom view

K=2.74mm

E2

Thermal pad, pins 1 and 2
are source; Pin 3 is sensing
source; Pin 4 is gate; Pins 5
to 8 are drain

CO.34x45°

b   e

L

4   1

D2

7.000

1.200   2.000

1.050

7.950   3.200
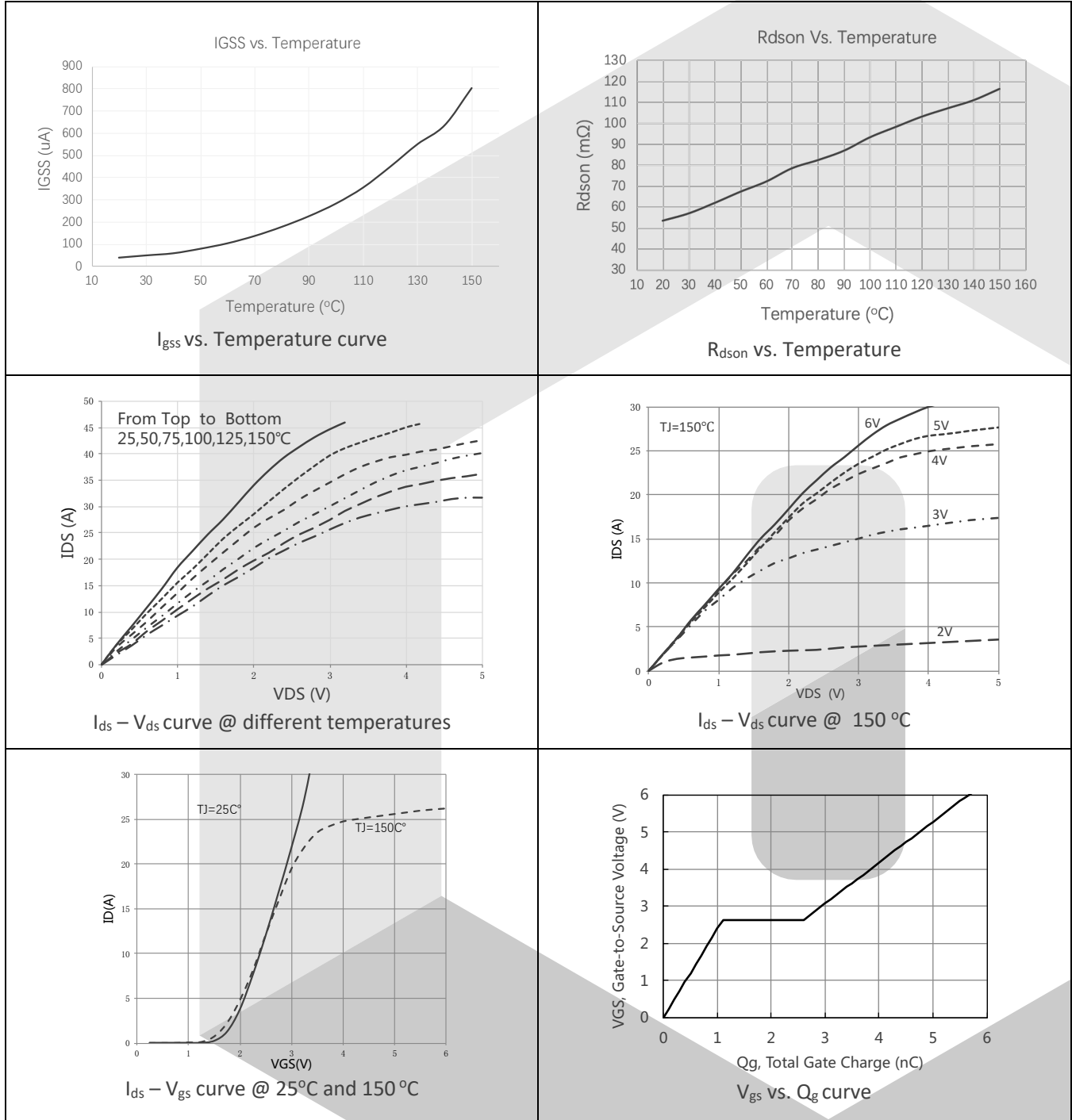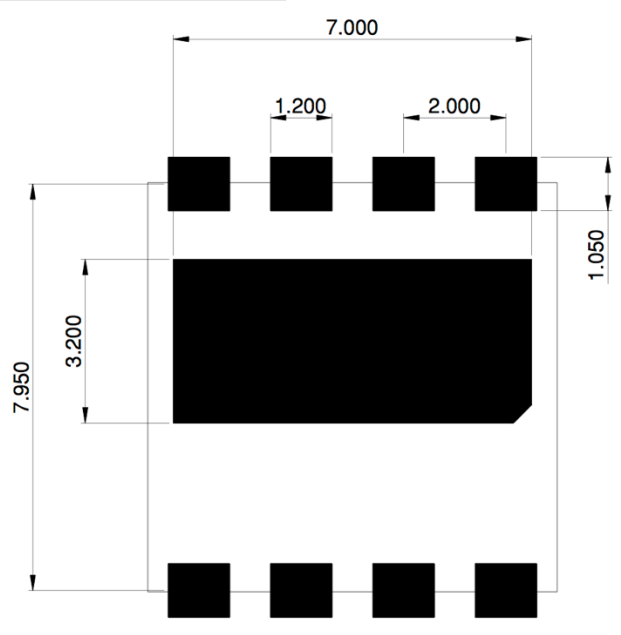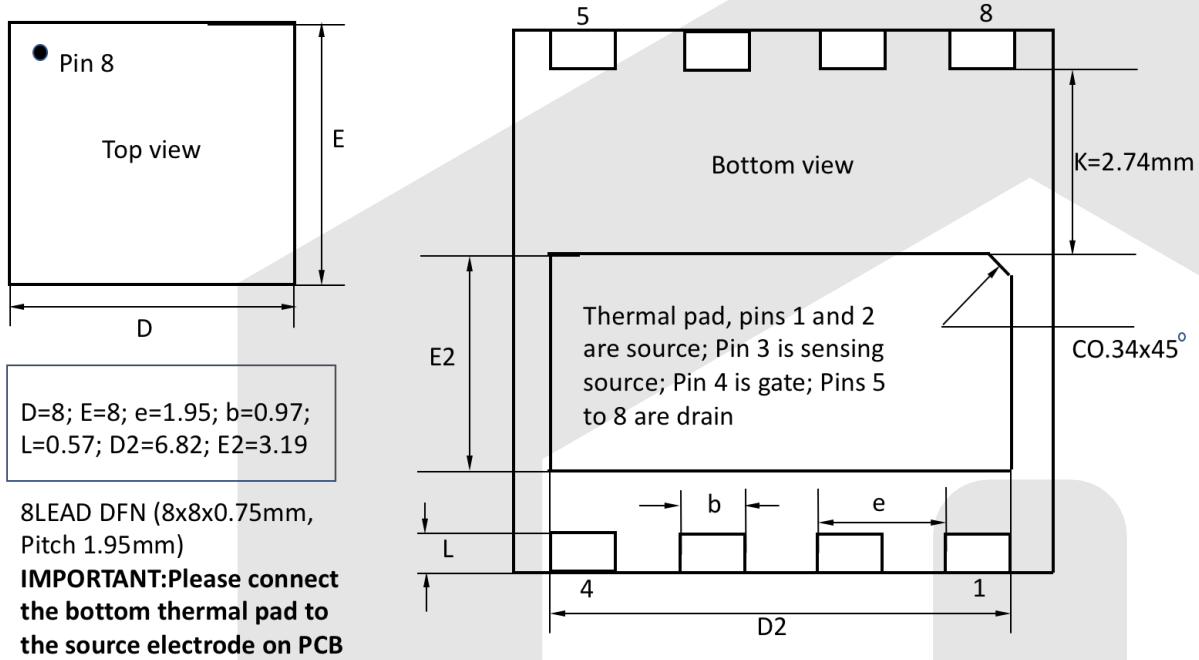
GaN HEMT Frequently Asked Questions

1	Q: Can we do pin to pin switch for silicon MOSFET or IGBT? A: The short answer is no. GaN HEMT power devices are far superior than the best silicon devices such as super junction MOSFETs. However, due to different requirements of gate driving voltage and extremely high dv/dt slew rate, special drivers and optimized PCB layouts are recommended to minimize the impact from circuit parasitics. Some packaging forms such as GaNPower's DFN packaged devices offer both sense and force for the source terminal. Also, for traditional TO220 packages, please be advised that the pins are arranged as Gate – Source -Drain, and the thermal pad is connected to the source instead of drain.
2	Q: Are GaN power devices reliable? A: GaN power HEMTs have been tested by GaNPower and many other vendors, users and testing facilities to be as reliable (if not better than) silicon counterparts.
3	Q: How do GaN power devices compare with SiC? A: Currently GaN power HEMT devices are most suitable for low to medium voltage ($\leqslant$1200V) and power (<20KW) applications. GaN is the ideal choice for high frequency applications. SiC devices are better choice for high voltage and high-power applications (>20KW).
4	Q: Do we need to parallel an FRD for applications such as inverters? A: GaN devices are different from silicon MOSFET or IGBT in that they have no inherent PN junction diodes that cause reverse recovery issue. User do not need to parallel an FRD for the purpose of suppressing the body diode reverse recovery effect, since GaN HEMT can operate in both first and third quadrants. However, care should be taken for the dead time power loss since the Vsd voltage of GaN HEMT is usually close to 2V. This is especially true when a negative gate voltage is applied.
6	Q: Can we parallel GaN HEMT devices? A: Yes, GaN HEMT is ideal for paralleling, due to positive temperature coefficient of Rdson and slightly positive temperature coefficient of threshold voltage.

5	Q: Where can we find drivers for GaNPower HEMT devices?
	A: While some of the GaNPower's HEMTs are either monolithically integrated with gate driver or co-packaged with a silicon driver, drivers can be easily found from vendors such as TI and Silicon Lab for either single sided or half-bridge configurations:
	  ✓ TI: LM5114: Single 7.6A Peak Current Low-Side Gate Driver
	  ✓ TI: UCC27611: 5V, 4A/6A Low Side GaN Driver
	  ✓ Maxim: MAX5048C: 7A Sink/3A Source Current, 8ns, SOT23, MOSFET Drive
	  ✓ Fairchild: FAN3122: Single 9-A High-Speed, Low-Side Gate Driver
	  ✓ Silicon Lab: Si827X: 4 Amp ISO driver with High Transient (dv/dt) Immunity